

R1RW0416DI Series

Wide Temperature Range Version
4M High Speed SRAM (256-kword × 16-bit)

REJ03C0109-0201
Rev.2.01
Jun 16, 2010

Description

The R1RW0416DI is a 4-Mbit high speed static RAM organized 256-kword × 16-bit. It has realized high speed access time by employing CMOS process (6-transistor memory cell) and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The R1RW0416DI is packaged in 400-mil 44-pin SOJ and 400-mil 44-pin plastic TSOPII for high density surface mounting.

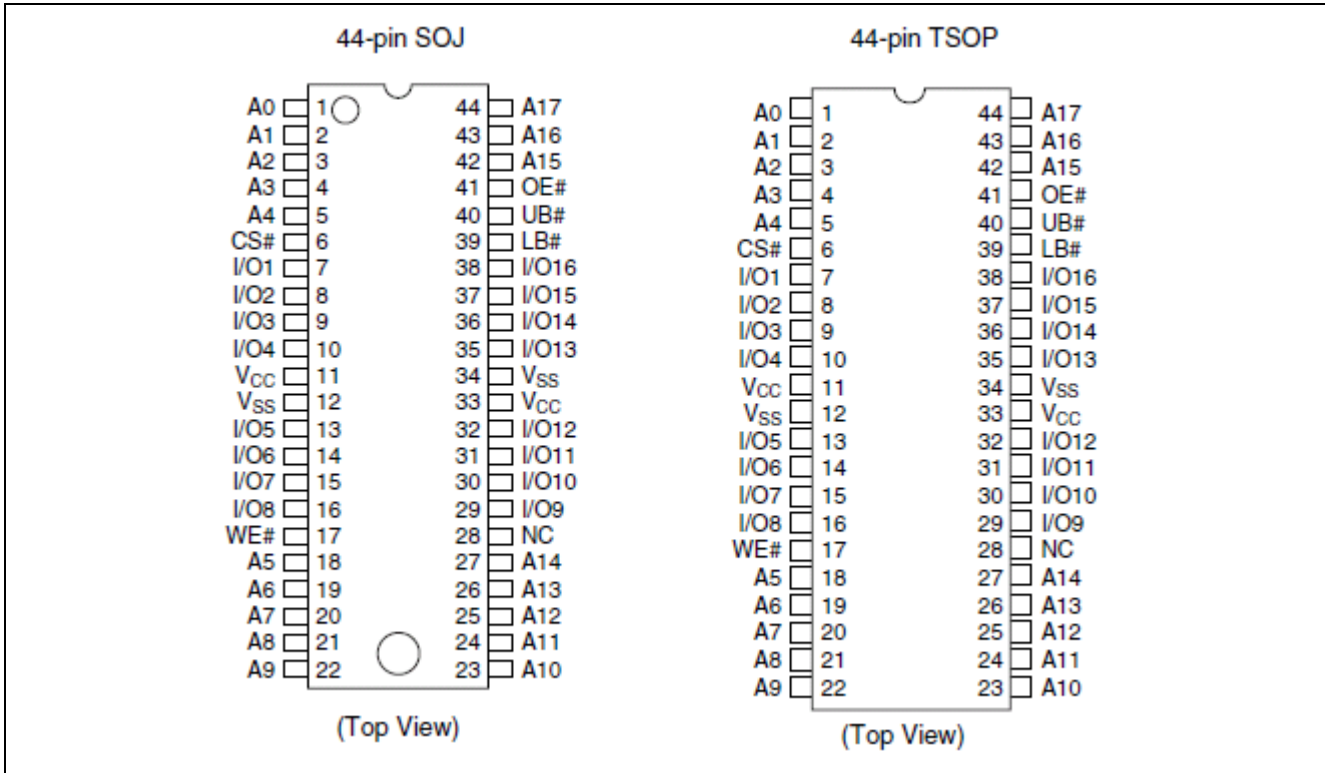
Features

- Single 3.3 V supply: 3.3 V ± 0.3 V
- Access time: 10ns/12 ns (max)
- Completely static memory
 - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
 - All inputs and outputs
- Operating current: 145/130 mA (max)
- TTL standby current: 40 mA (max)
- CMOS standby current: 5 mA (max)
- Center V_{CC} and V_{SS} type pin out
- Temperature range: -40 to +85°C

Ordering Information

Type No.	Access time	Package
R1RW0416DGE-0PI	10ns	400-mil 44-pin plastic SOJ (44P0K)
R1RW0416DGE-2PI	12 ns	
R1RW0416DSB-0PI	10 ns	400-mil 44-pin plastic TSOPII (44P3W-H)
R1RW0416DSB-2PI	12 ns	

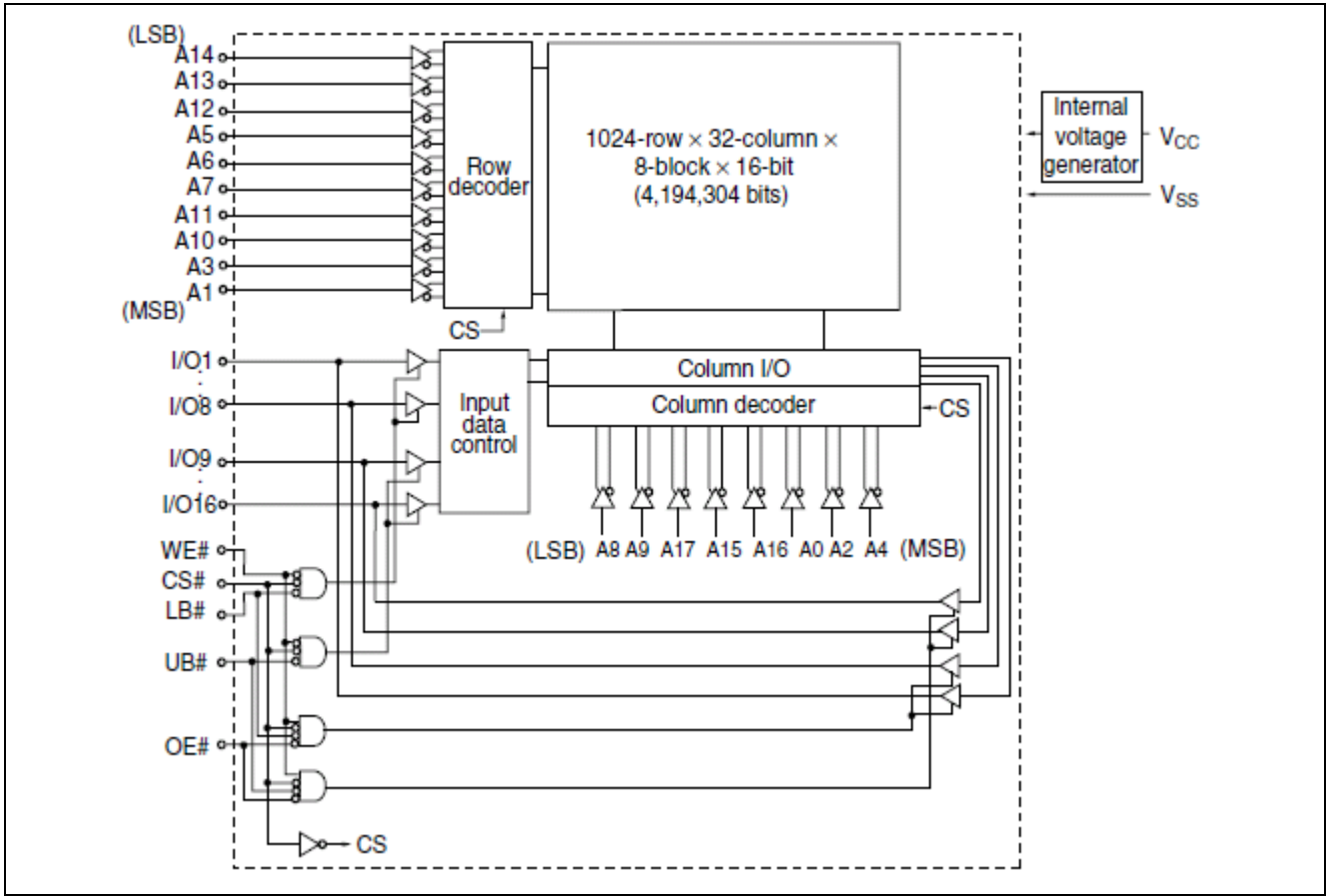
Pin Arrangement



Pin Description

Pin name	Function
A0 to A17	Address input
I/O1 to I/O16	Data input/output
CS#	Chip select
OE#	Output enable
WE#	Write enable
UB#	Upper byte select
LB#	Lower byte select
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

Block Diagram



Operation Table

CS#	OE#	WE#	LB#	UB#	Mode	V _{CC} current	I/O1–I/O8	I/O9–I/O16	Ref. Cycle
H	×	×	×	×	Standby	I _{SB} , I _{SB1}	High-Z	High-Z	—
L	H	H	×	×	Output disable	I _{CC}	High-Z	High-Z	—
L	L	H	L	L	Read	I _{CC}	Output	Output	Read cycle
L	L	H	L	H	Lower byte read	I _{CC}	Output	High-Z	Read cycle
L	L	H	H	L	Upper byte read	I _{CC}	High-Z	Output	Read cycle
L	L	H	H	H	—	I _{CC}	High-Z	High-Z	—
L	×	L	L	L	Write	I _{CC}	Input	Input	Write cycle
L	×	L	L	H	Lower byte write	I _{CC}	Input	High-Z	Write cycle
L	×	L	H	L	Upper byte write	I _{CC}	High-Z	Input	Write cycle
L	×	L	H	H	—	I _{CC}	High-Z	High-Z	—

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V _{SS}	V _{CC}	–0.5 to +4.6	V
Voltage on any pin relative to V _{SS}	V _T	–0.5* ¹ to V _{CC} + 0.5* ²	V
Power dissipation	P _T	1.0	W
Operating temperature	T _{opr}	–40 to +85	°C
Storage temperature	T _{stg}	–55 to +125	°C
Storage temperature under bias	T _{bias}	–40 to +85	°C

Notes: 1. V_T (min) = –2.0 V for pulse width (under shoot) ≤ 6 ns

2. V_T (max) = V_{CC} + 2.0 V for pulse width (over shoot) ≤ 6 ns

Recommended DC Operating Conditions

(Ta = -40 to +85°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}^{*3}	3.0	3.3	3.6	V
	V_{SS}^{*4}	0	0	0	V
Input voltage	V_{IH}	2.0	—	$V_{CC} + 0.5^{*2}$	V
	V_{IL}	-0.5^{*1}	—	0.8	V

- Notes: 1. V_{IL} (min) = -2.0 V for pulse width (under shoot) ≤ 6 ns
 2. V_{IH} (max) = $V_{CC} + 2.0$ V for pulse width (over shoot) ≤ 6 ns
 3. The supply voltage with all V_{CC} pins must be on the same level.
 4. The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics

(Ta = -40 to +85°C, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$)

Parameter	Symbol	Min	Max	Unit	Test conditions
Input leakage current	$ I_{LI} $	—	2	μA	$V_{IN} = V_{SS}$ to V_{CC}
Output leakage current	$ I_{LO} $	—	2	μA	$V_{IN} = V_{SS}$ to V_{CC}
Operating power supply current	I_{CC}	—	130	mA	Min cycle CS# = V_{IL} , $I_{OUT} = 0 \text{ mA}$ Other inputs = V_{IH}/V_{IL}
Standby power supply current	I_{SB}	—	40	mA	Min cycle, CS# = V_{IH} , Other inputs = V_{IH}/V_{IL}
	I_{SB1}	—	5	mA	f = 0 MHz $V_{CC} \geq \text{CS\#} \geq V_{CC} - 0.2 \text{ V}$, (1) $0 \text{ V} \leq V_{IN} \leq 0.2 \text{ V}$ or (2) $V_{CC} \geq V_{IN} \geq V_{CC} - 0.2 \text{ V}$
Output voltage	V_{OL}	—	0.4	V	$I_{OL} = 8 \text{ mA}$
	V_{OH}	2.4	—	V	$I_{OH} = -4 \text{ mA}$

Capacitance

(Ta = +25°C, f = 1.0 MHz)

Parameter	Symbol	Min	Max	Unit	Test conditions
Input capacitance ^{*1}	C_{IN}	—	6	pF	$V_{IN} = 0 \text{ V}$
Input/output capacitance ^{*1}	$C_{I/O}$	—	8	pF	$V_{I/O} = 0 \text{ V}$

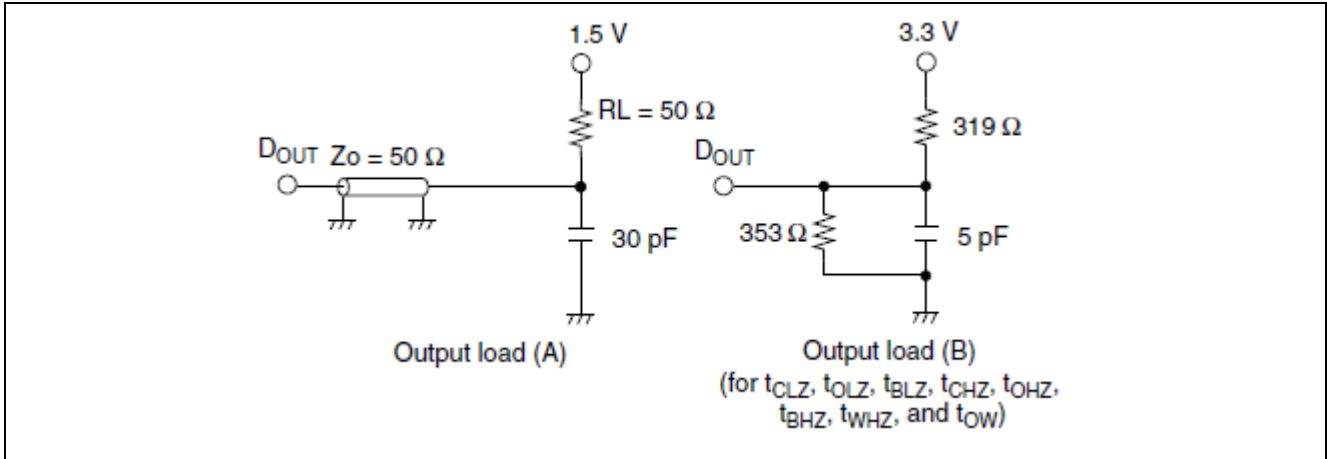
Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics

($T_a = -40$ to $+85^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, unless otherwise noted.)

Test Conditions

- Input pulse levels: 3.0 V/0.0 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	R1RW0416DI				Unit	Notes
		10ns Version		12ns Version			
		Min	Max	Min	Max		
Read cycle time	t_{RC}	10	—	12	—	ns	
Address access time	t_{AA}	—	10	—	12	ns	
Chip select access time	t_{ACS}	—	10	—	12	ns	
Output enable to output valid	t_{OE}	—	5	—	6	ns	
Byte select to output valid	t_{BA}	—	5	—	6	ns	
Output hold from address change	t_{OH}	3	—	3	—	ns	
Chip select to output in low-Z	t_{CLZ}	3	—	3	—	ns	1
Output enable to output in low-Z	t_{OLZ}	0	—	0	—	ns	1
Byte select to output in low-Z	t_{BLZ}	0	—	0	—	ns	1
Chip deselect to output in high-Z	t_{CHZ}	—	5	—	6	ns	1
Output disable to output in high-Z	t_{OHZ}	—	5	—	6	ns	1
Byte deselect to output in high-Z	t_{BHZ}	—	5	—	6	ns	1

Write Cycle

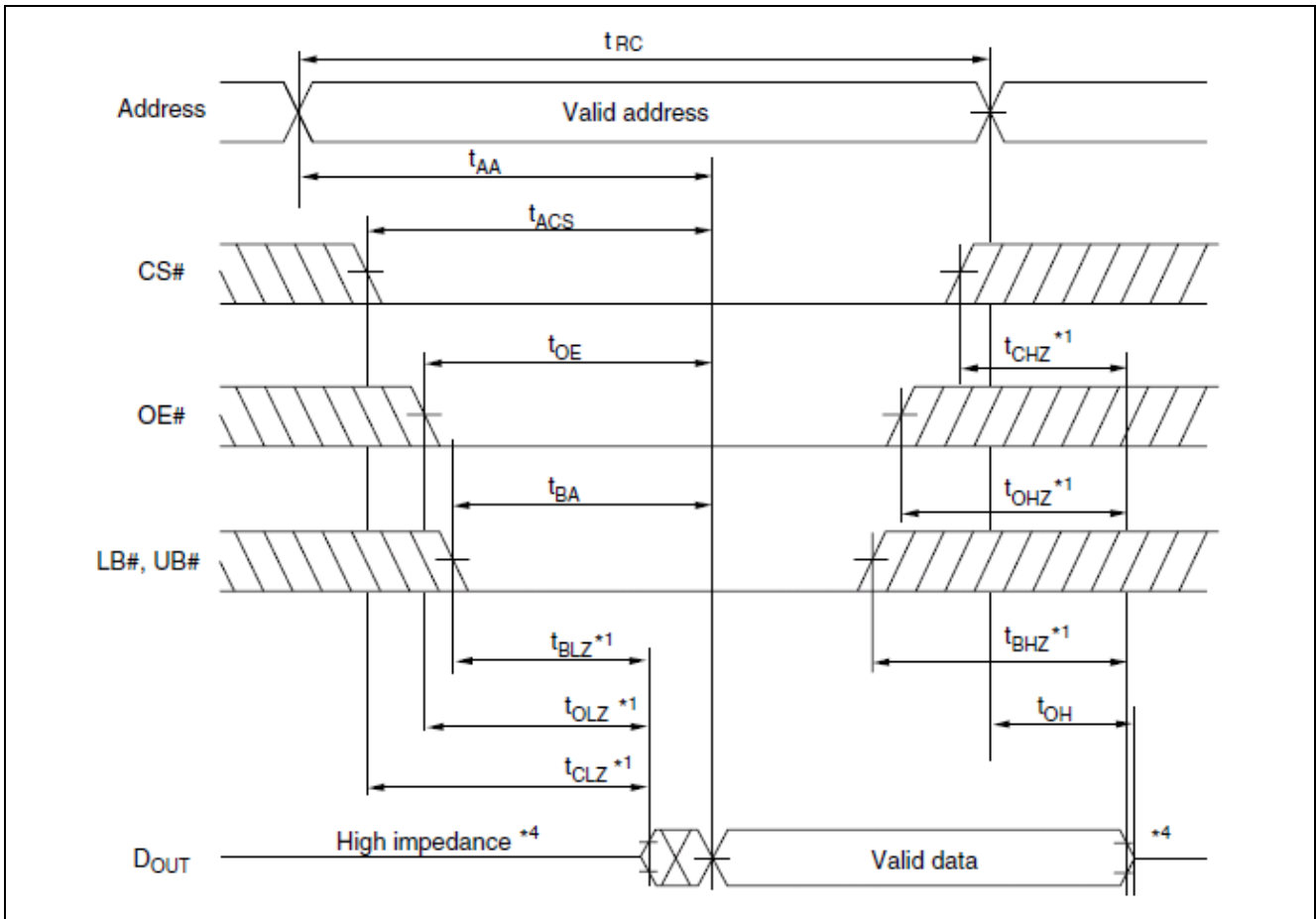
Parameter	Symbol	R1RW0416DI				Unit	Notes
		10ns Version		12ns Version			
		Min	Max	Min	Max		
Write cycle time	t _{WC}	10	—	12	—	ns	
Address valid to end of write	t _{AW}	7	—	8	—	ns	
Chip select to end of write	t _{CW}	7	—	8	—	ns	8
Write pulse width	t _{WP}	7	—	8	—	ns	7
Byte select to end of write	t _{BW}	7	—	8	—	ns	
Address setup time	t _{AS}	0	—	0	—	ns	5
Write recovery time	t _{WR}	0	—	0	—	ns	6
Data to write time overlap	t _{DW}	5	—	6	—	ns	
Data hold from write time	t _{DH}	0	—	0	—	ns	
Write disable to output in low-Z	t _{OW}	3	—	3	—	ns	1
Output disable to output in high-Z	t _{OZH}	—	5	—	6	ns	1
Write enable to output in high-Z	t _{WHZ}	—	5	—	6	ns	1

Notes: 1. Transition is measured ± 200 mV from steady voltage with output load (B). This parameter is sampled and not 100% tested.

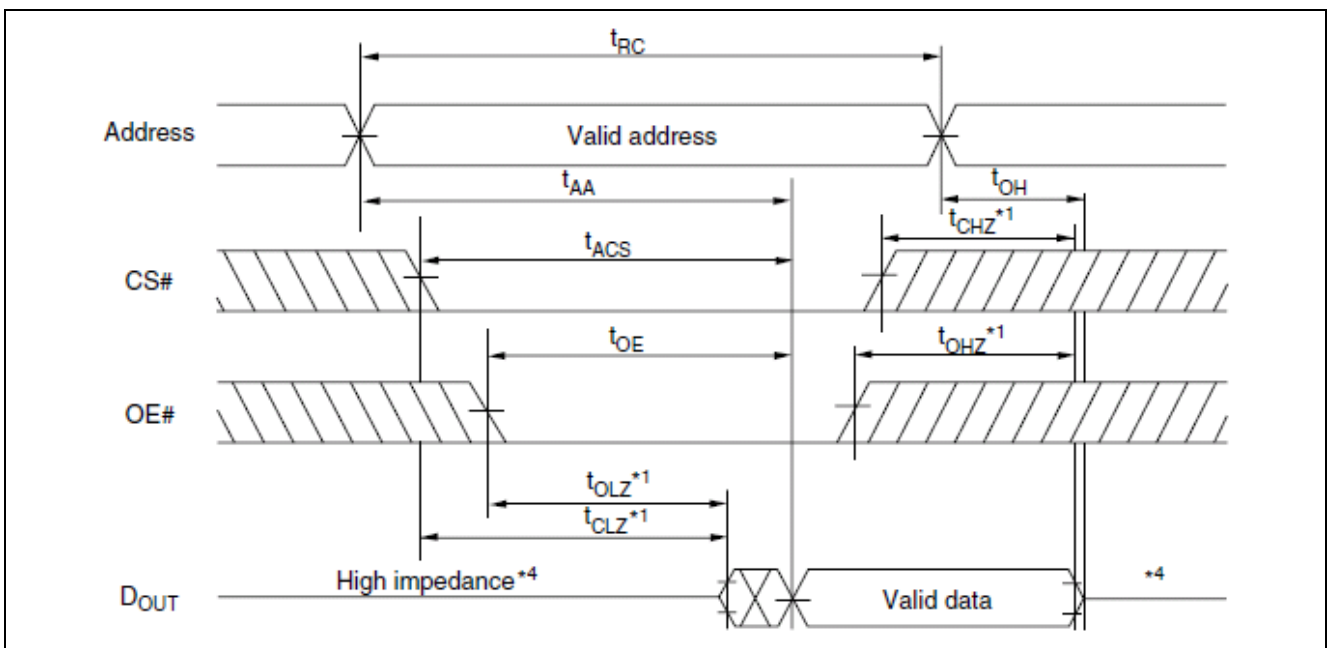
2. If the CS# or LB# or UB# low transition occurs simultaneously with the WE# low transition or after the WE# transition, output remains a high impedance state.
3. WE# and/or CS# must be high during address transition time.
4. If CS#, OE#, LB# and UB# are low during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.
5. t_{AS} is measured from the latest address transition to the latest of CS#, WE#, LB# or UB# going low.
6. t_{WR} is measured from the earliest of CS#, WE#, LB# or UB# going high to the first address transition.
7. A write occurs during the overlap of a low CS#, a low WE# and a low LB# or a low UB# (t_{WP}). A write begins at the latest transition among CS# going low, WE# going low and LB# going low or UB# going low. A write ends at the earliest transition among CS# going high, WE# going high and LB# going high or UB# going high.
8. t_{CW} is measured from the later of CS# going low to the end of write.

Timing Waveforms

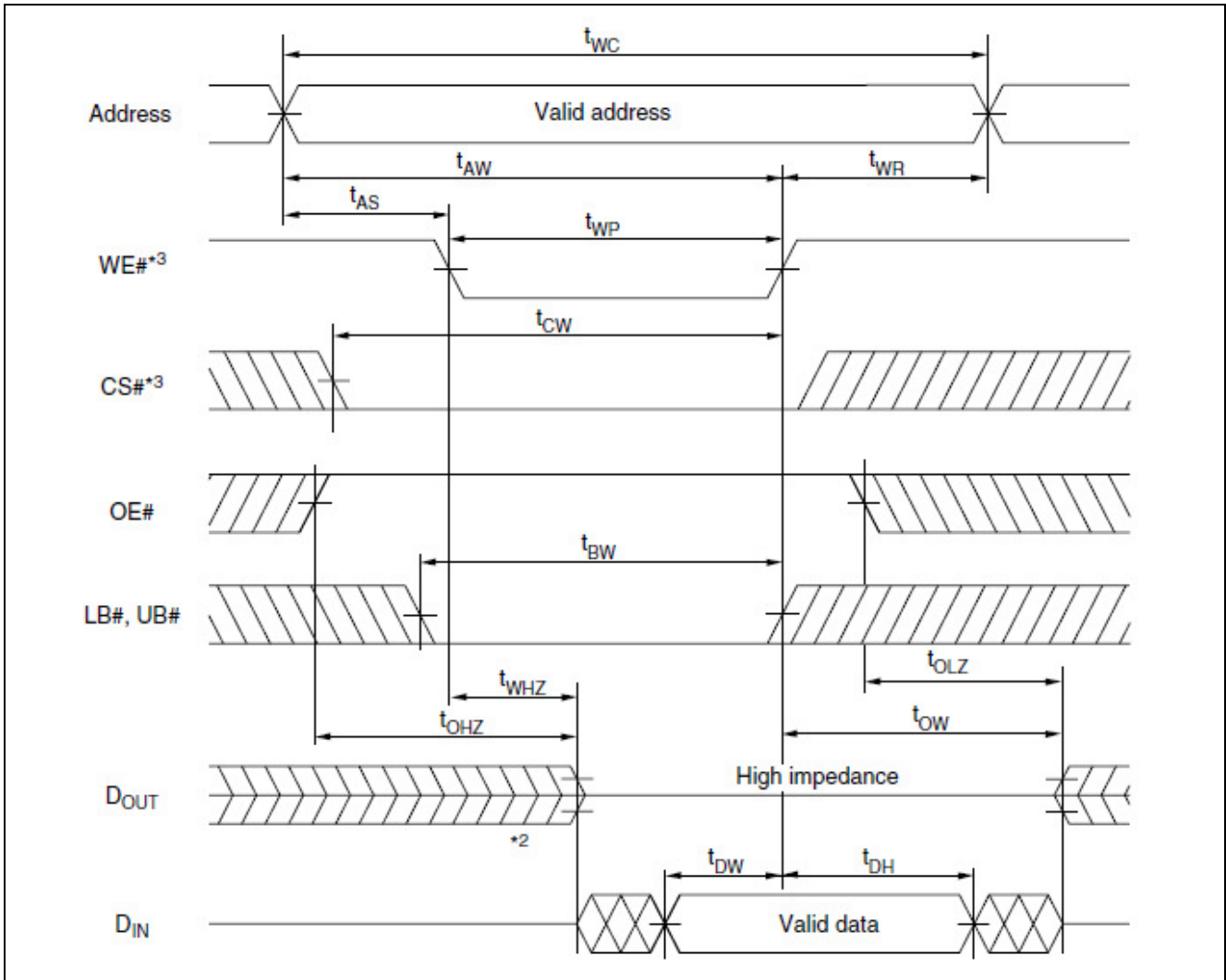
Read Timing Waveform (1) (WE# = V_{IH})



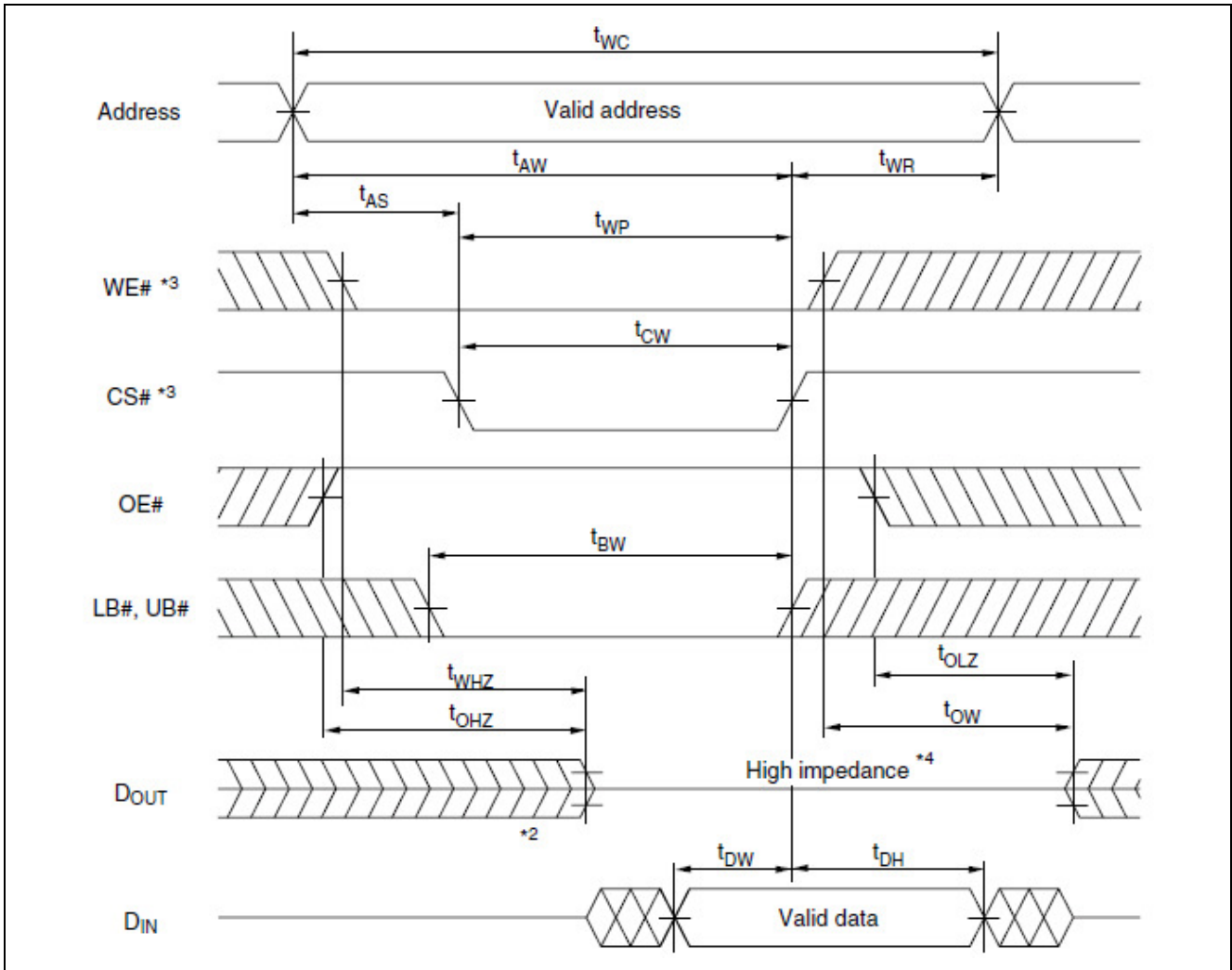
Read Timing Waveform (2) (WE# = V_{IH}, LB# = V_{IL}, UB# = V_{IL})



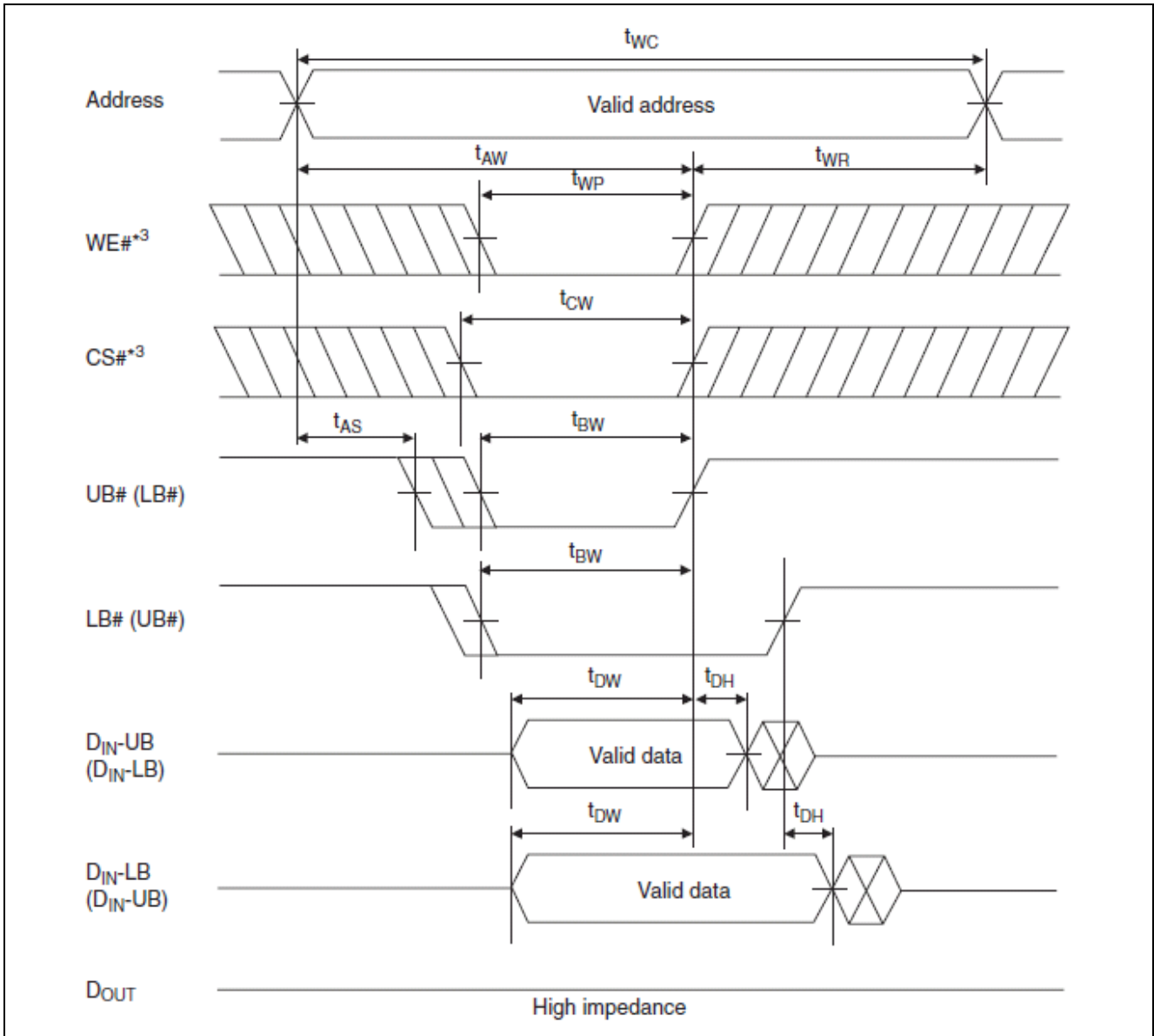
Write Timing Waveform (1) (WE# Controlled)



Write Timing Waveform (2) (CS# Controlled)



Write Timing Waveform (3) (LB#, UB# Controlled, OE# = V_{IH})



Revision History	R1RW0416DI Series data sheet
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Rev.	Date	Description	
		Page	Summary
0.01	Sep. 30, 2003	-	Initial issue
1.00	Mar. 12, 2004	--	Deletion of Preliminary
2.00	May. 01, 2009	- P1 P5 P6/P7	Addition of access grade 10ns version. The product lineup :R1RW0416DSB-0PI/DGE-0PI is added. Operating power supply current of 10ns cycle version is described to the DC characteristic. The timing standard of 10ns version is described at the read cycle The timing standard of 10ns version is described at the write cycle
2.01	Jun. 16, 2010	-	Change the format, 'Renesas Electronics Corporation',

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhichunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852-2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
7F, No. 363 Fu Shing North Road Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel'or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141